

IPT059N15N3ATMA1

Data Sheet

RFO

N-Channel MOSFET, 155 A, 150 V OptiMOS 3, 8-Pin HSOF Infineon

Manufacturers	Infineon Technologies Corporation	No. of a
Package/Case	PG-HSOF-8-1	2220
Product Type	Transistors	
RoHS		
Lifecycle		Images are for reference only

Please submit RFQ for IPT059N15N3ATMA1 or Email to us: sales@ovaga.com We will contact you in 12 hours.

General Description

Infineon's TO-Leadless package is optimized for high current applications such as forklift, light electric vehicles (LEV), POL (point-of-load) and telecom. This package is a perfect solution for high power applications where highest efficiency, outstanding EMI behaviour as well as best thermal behaviour and space reduction are required.

Features

Industry's lowest R DS(on)

Highest current capability >480A

Very low package parasitics and inductances

Less paralleling and cooling required

Highest system reliability

System cost reduction

Enabling very compact design

Related Products

Application

Point-of-load (POL)

Telecom

efuse



IPP60R070CFD7

Infineon Technologies Corporation TO-220-3



IPB180N06S4-H1

Infineon Technologies Corporation PG-TO263-7-3



IPG20N04S4-12

Infineon Technologies Corporation TDSON-8



IPD25N06S4L-30 Infineon Technologies Corporation PG-TO252-3



IPP60R074C6

Infineon Technologies Corporation TO-220-3







IPW65R080CFD

Infineon Technologies Corporation TO-247

IPD180N10N3G

Infineon Technologies Corporation TO-252

IPD70R1K4P7S

Infineon Technologies Corporation TO252-3